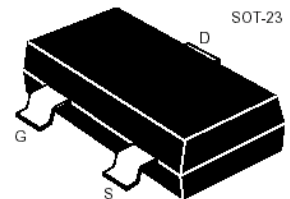


P-Channel Enhancement-Mode MOS FETs

MAXIMUM RATINGS

Characteristic	Symbol	Max	Unit
Drain-Source Voltage	BV_{DSS}	-50	V
Gate- Source Voltage	V_{GS}	± 20	V
Drain Current (continuous)	I_{DR}	-130	mA
Drain Current (pulsed)	I_{DRM}	-520	mA

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation $T_A = 25^\circ\text{C}$	P_D	200	mW
Derate above 25°C		1.8	mW/ $^\circ\text{C}$
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	350	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	T_J, T_{stg}	150 $^\circ\text{C}$, -55to+150 $^\circ\text{C}$	

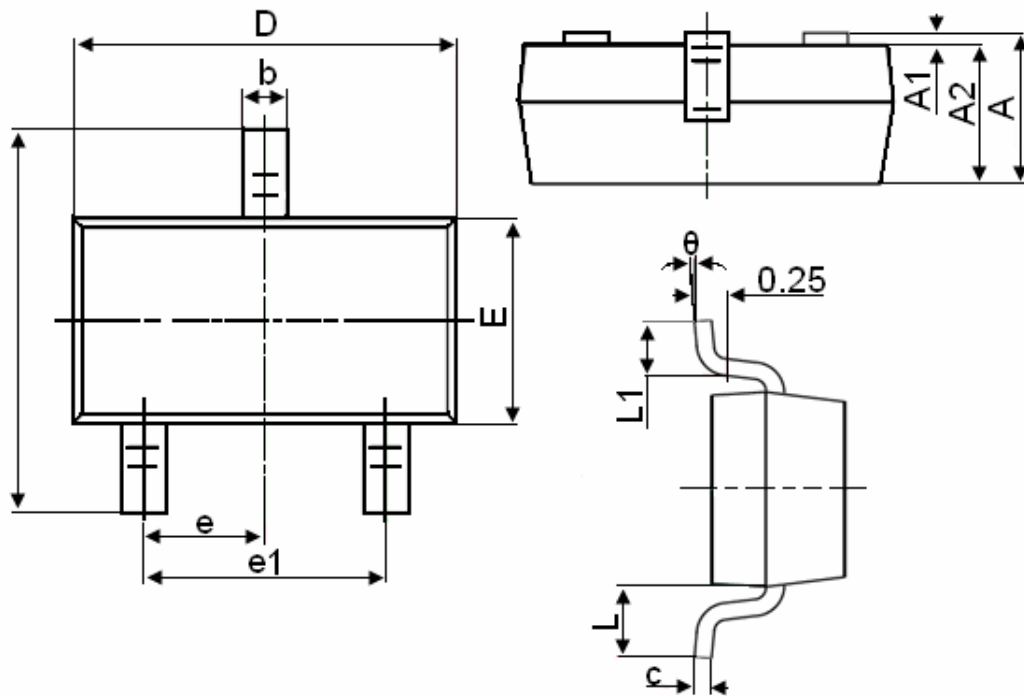
ELECTRICAL CHARACTERISTICS

 (T_A=25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage (I _D = -250µA, V _{GS} = 0V)	BV _{DSS}	-50	—	—	V
Gate Threshold Voltage (I _D = -250µA, V _{GS} = V _{DS})	V _{GS(th)}	-1.0	—	-2.5	V
Diode Forward Voltage Drop (I _{SD} = -200mA, V _{GS} = 0V)	V _{SD}	—	—	-1.5	V
Zero Gate Voltage Drain Current (V _{GS} = 0V, V _{DS} = -50V) (V _{GS} = 0V, V _{DS} = -50V, T _A = 125°C)	I _{DSS}	—	—	-15 -60	µA
Gate Body Leakage (V _{GS} = ±20V, V _{DS} = 0V)	I _{GSS}	—	—	±10	nA
Static Drain-Source On-State Resistance (I _D = -100mA, V _{GS} = -5V)	R _{DS(ON)}	—	—	10	Ω
Input Capacitance (V _{GS} = 0V, V _{DS} = -25V, f = 1MHz)	C _{ISS}	—	73	—	pF
Common Source Output Capacitance (V _{GS} = 0V, V _{DS} = -25V, f = 1MHz)	C _{OSS}	—	10	—	pF
Turn-ON Time (V _{DS} = -30V, I _D = -270mA, R _{GEN} = 6Ω)	t _(on)	—	—	5	ns
Turn-OFF Time (V _{DS} = -30V, I _D = -270mA, R _{GEN} = 6Ω)	t _(off)	—	—	20	ns
Reverse Recovery Time (I _{SD} = -100mA, V _{GS} = 0V)	t _{rr}	—	10	—	ns

1. FR-5=1.0×0.75×0.062in.
2. Alumina=0.4×0.3×0.024in.99.5%alumina.
3. Pulse Width≤300 µs; Duty Cycle≤2.0%.

SOT-23 Package Information



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.500
θ	0°	8°